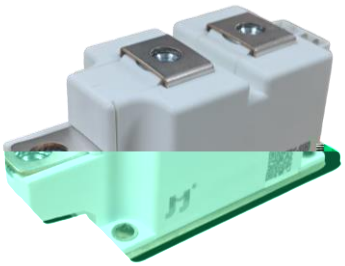
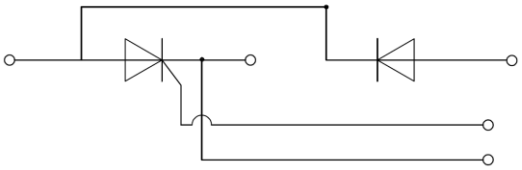
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**FIG.1:**Power dissipation vs. on-state current (per thyristor or diode)

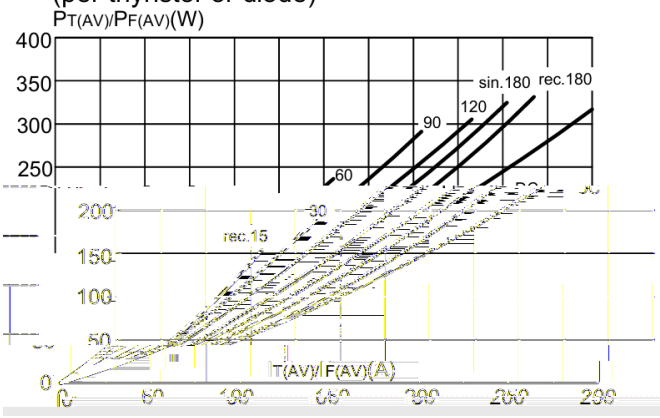



**FIG.2:** Maximum transient thermal impedance junction to case(per thyristor or diode)

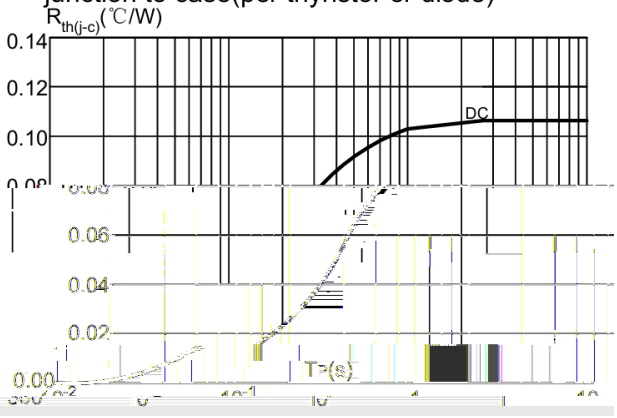



**FIG.3:**Forward characteristics (per thyristor or diode)

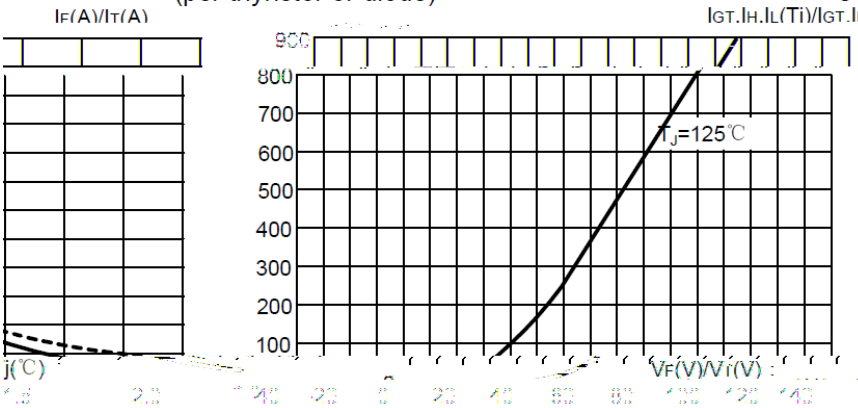
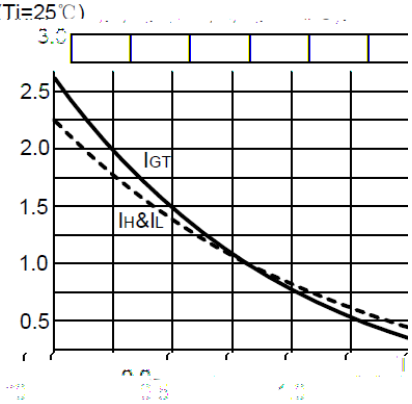
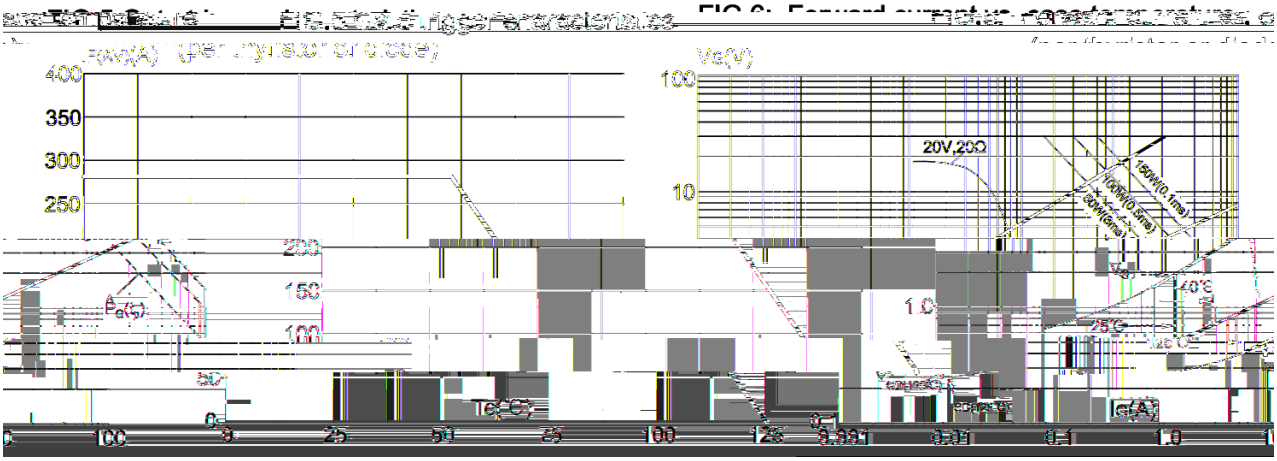
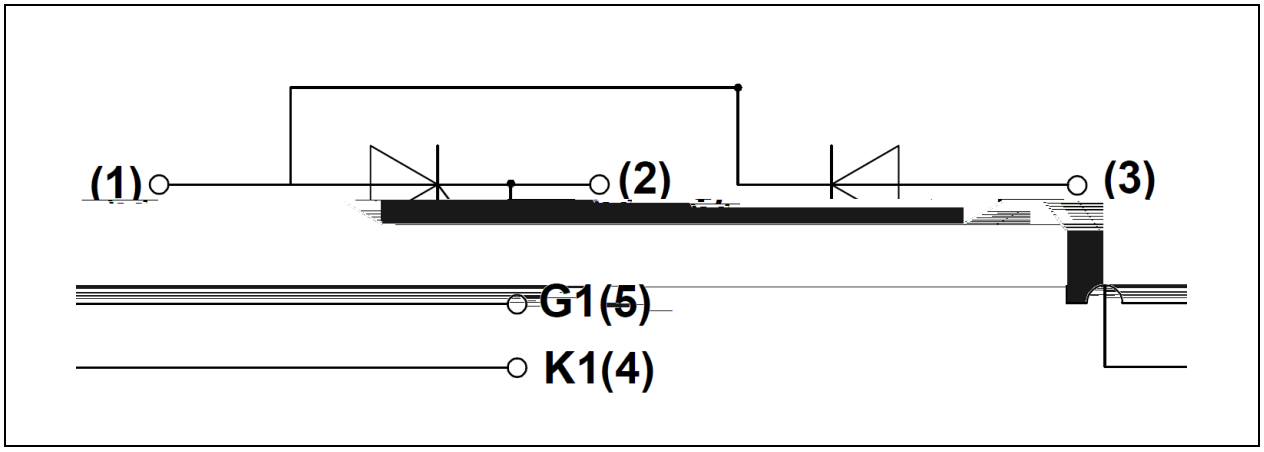
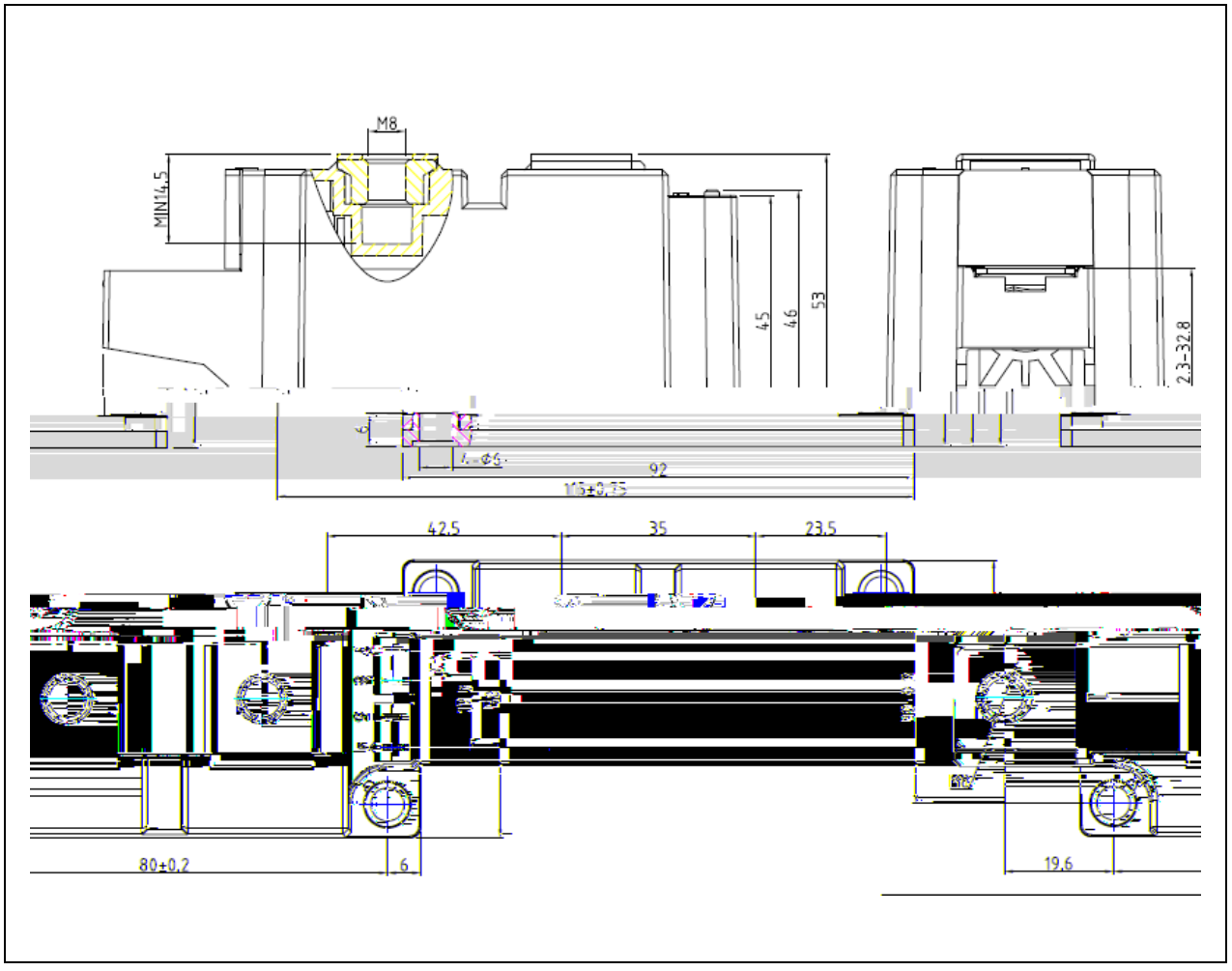



**FIG.4:** Relative variations of gate trigger current, holding current and latching current versus junction temperature




(1)
(2)
(3)
G1(5)
K1(4)


M8
MIN14.5
45
46
53
2.3-32.8
92
42.5
35
23.5
80±0.2
6
19.6